

## SUPPORTING INFORMATION

# A High-performance Polarization-sensitive and Stable Self-powered UV Photodetector Based on Dendritic Crystal Lead-free Perovskites $\text{CsCu}_2\text{I}_3$ /GaN Heterostructure

Can Zou<sup>a,1</sup>, Qing Liu<sup>a,1</sup>, Kai Chen<sup>a</sup>, Fei Chen<sup>a</sup>, Zixuan Zhao<sup>a</sup>, Yunxuan Cao<sup>a</sup>, Congcong Deng<sup>a</sup>, Xingfu Wang<sup>a</sup>, Xiaohang Li<sup>b</sup>, Shaobin Zhan<sup>c, #</sup>, Fangliang Gao<sup>a, #</sup>, Shuti Li<sup>a,d, #</sup>

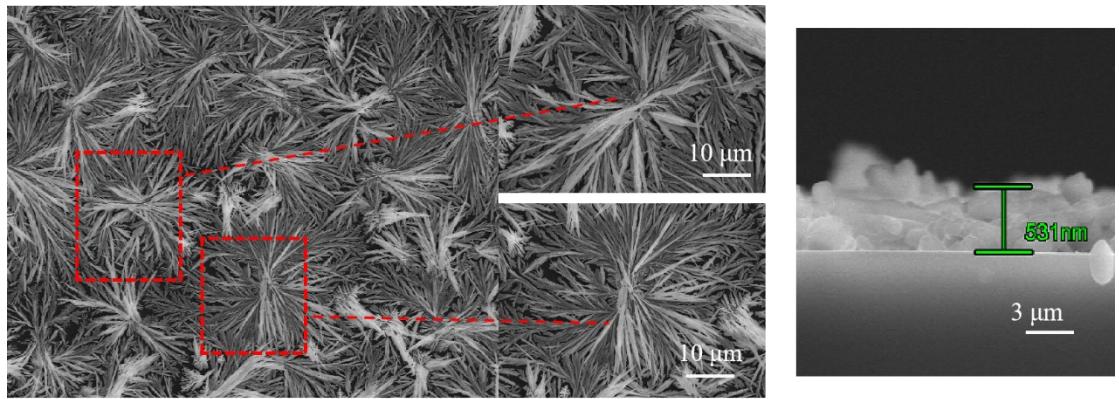
<sup>a</sup> Guangdong Engineering Research Center of Optoelectronic Functional Materials and Devices, Institute of Semiconductors, South China Normal University, Guangzhou, 510631, People's Republic of China. E-mail: gaofl@m.scnu.edu.cn

<sup>b</sup> King Abdullah University of Science and Technology (KAUST), Advanced Semiconductor Laboratory, Thuwal 23955, Saudi Arabia

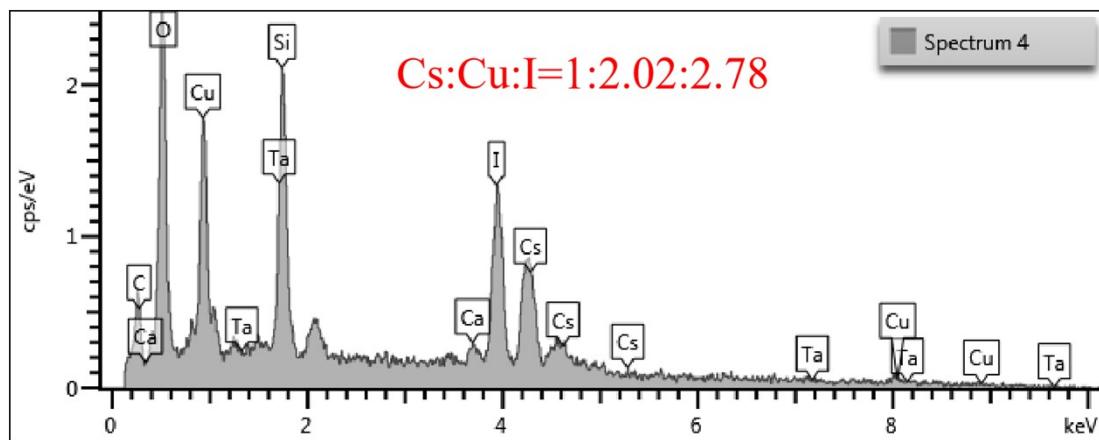
<sup>c</sup> Shenzhen Institute of Information Technology, Innovation and Entrepreneurship School, Shenzhen, 518172, People's Republic of China.  
E-mail: 13266960452@163.com

<sup>d</sup> 21C Innovation Laboratory, Contemporary Amperex Technology Ltd, Ningde, Fujian, 352100, People's Republic of China. E-mail: lishuti@m.scnu.edu.cn

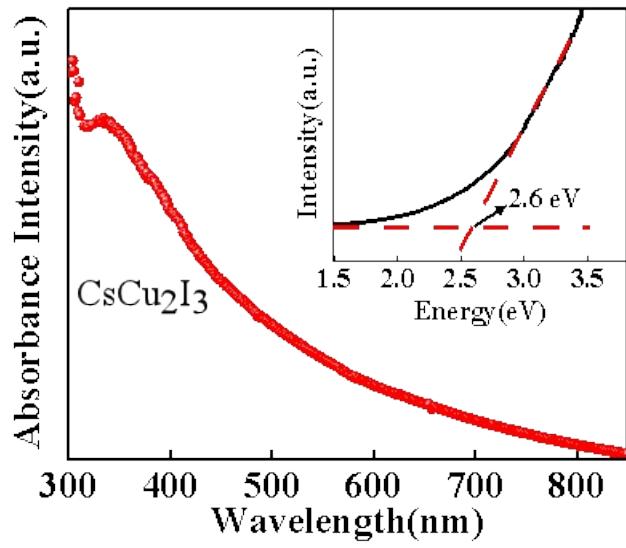
<sup>1</sup> These authors contributed equally to this work.



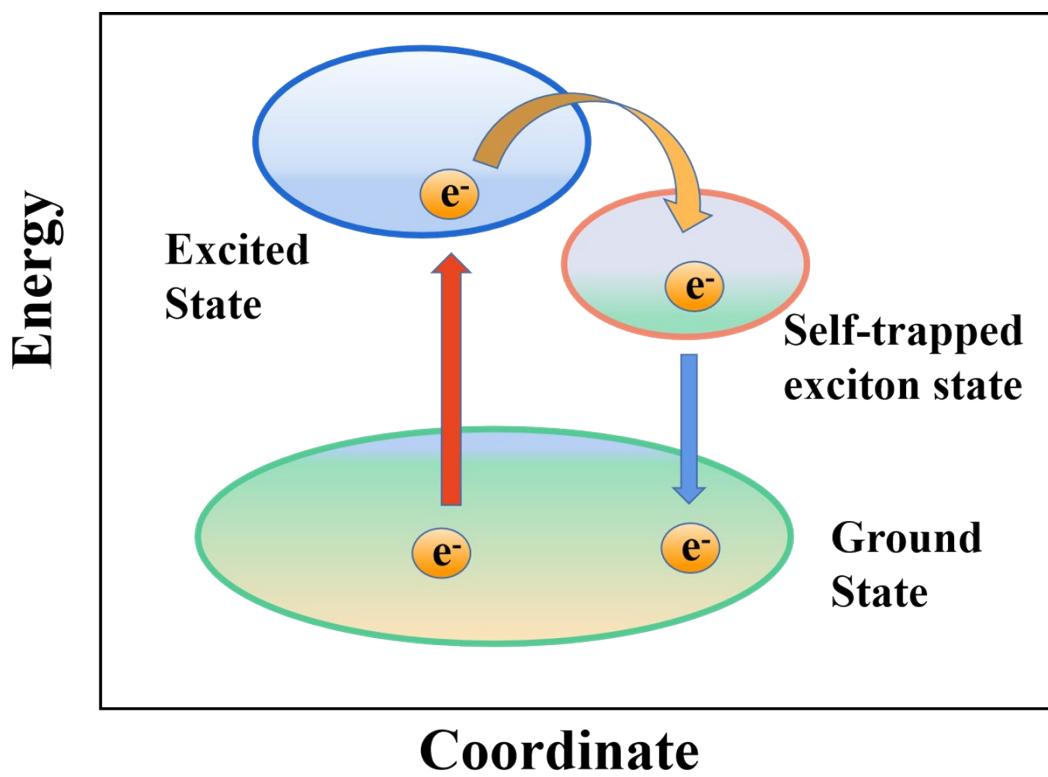
**Fig. S1.** The SEM images of pure  $\text{CsCu}_2\text{I}_3$  dendrites viewed from the top and side.



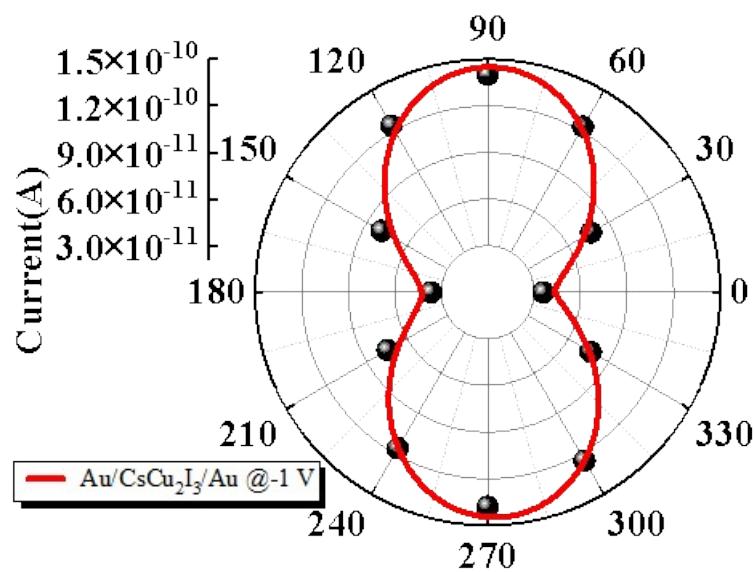
**Fig. S2. EDS spectrum of the  $\text{CsCu}_2\text{I}_3$  films annealed at 100 °C.**



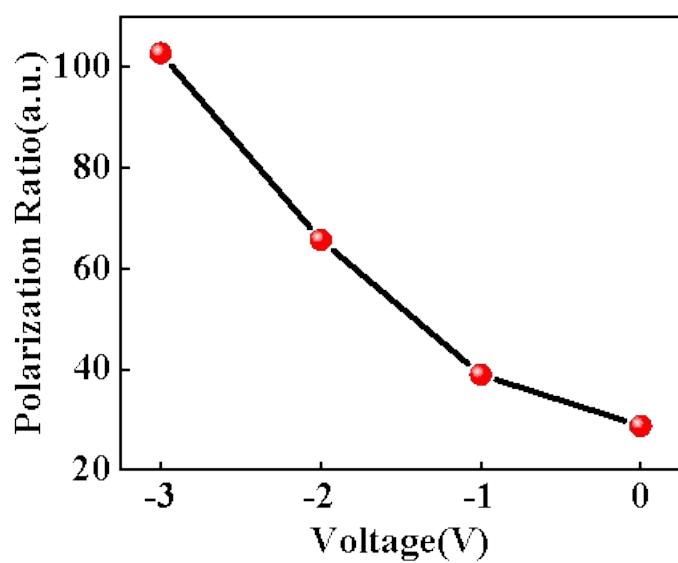
**Fig. S3. Energy band alignment of the  $\text{CsCu}_2\text{I}_3/\text{GaN}$  heterojunction.**



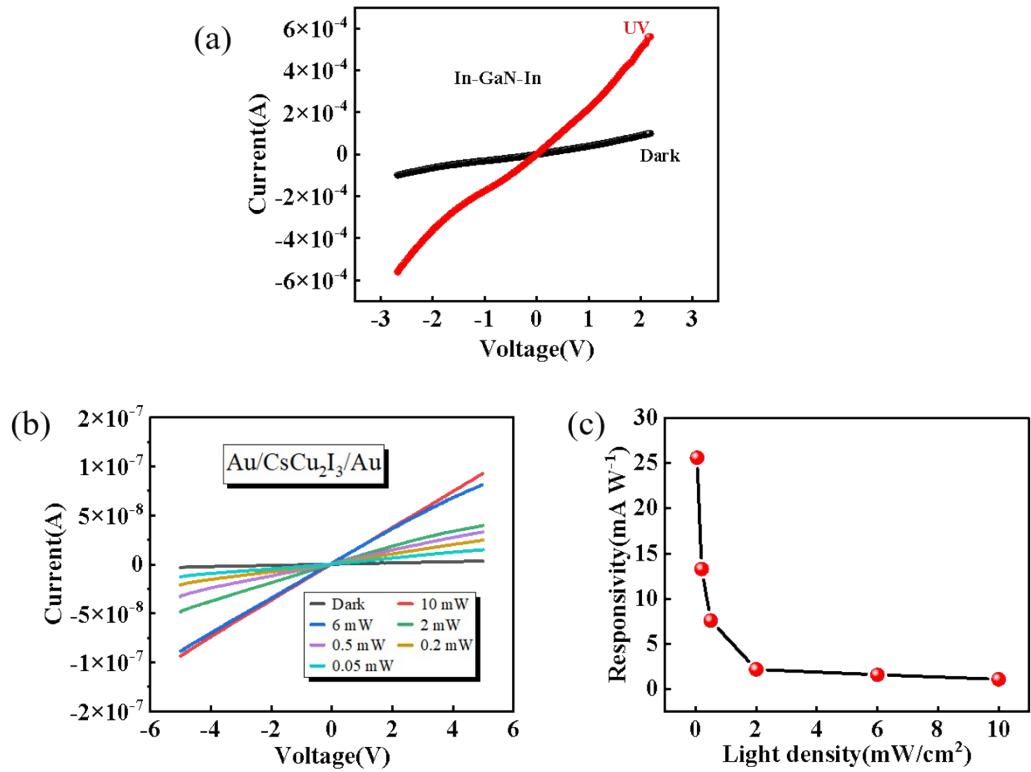
**Fig. S4.** Configuration coordinate diagram illustrating the STE transition process of  $\text{CsCu}_2\text{I}_3$ .



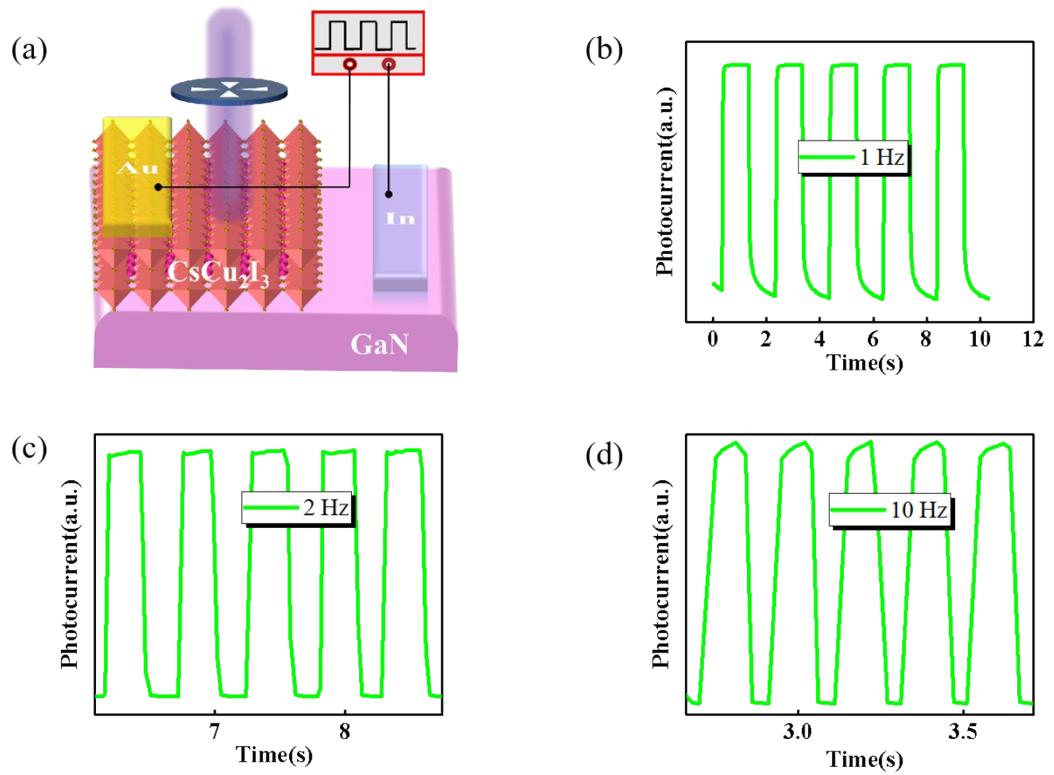
**Fig. S5.** The polarization anisotropy properties of pure  $\text{CsCu}_2\text{I}_3$  dendrites.



**Fig. S6. The variation of anisotropy ratio with voltage.**



**Fig. S7. The photoelectric properties of pure (a) GaN and (b)  $\text{CsCu}_2\text{I}_3$ . (c) Responsivity of the pure  $\text{CsCu}_2\text{I}_3$  dendrites photodetector versus light irradiation power.**



**Fig. S8. (a)** Schematic diagram of the device for measuring the response speed. Response of the photodetector irradiated by a 325 nm light with the modulation frequencies of (b) 1 Hz, (c) 2 Hz and (d) 10Hz at zero bias.